

Katerina Raleva

List of Publications by Year in descending order

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Version: 2024-02-01

21
papers

281
citations

1307594

7
h-index

1588992

8
g-index

23
all docs

23
docs citations

23
times ranked

202
citing authors

#	ARTICLE	IF	CITATIONS
1	Understanding the role of nitrogen and sulfur doping in promoting kinetics of oxygen reduction reaction and sodium ion battery performance of hollow spherical graphene. Carbon, 2022, 187, 230-240.	10.3	24
2	Investigation of the Mechanical Integrity of Prismatic Li-Ion Batteries Under Multi-Position Indentation. Journal of Electrochemical Energy Conversion and Storage, 2021, 18, .	2.1	0
3	Phonon Dissipation in Nanostructured Semiconductor Devices: Dispersing Heat Is Critical for Continued Integrated Circuit Progress. IEEE Nanotechnology Magazine, 2019, 13, 6-17.	1.3	3
4	Learning microelectronics with open educational resources in the cloud. , 2018, , .		0
5	SELF-HEATING EFFECTS IN SILICON NANOSCALE MOSFET(A MULTISCALE MODELING APPROACH). Journal of Electrical Engineering and Information Technologies, 2018, 3, 31-40.	0.1	0
6	Monte Carlo Device Simulations. , 2017, , 773-806.		0
7	Interplay of Self-Heating and Short-Range Coulomb Interactions due to Traps in a 10 nm Channel Length Nanowire Transistor. , 2017, , 711-715.		0
8	Modeling Self-Heating Effects in Nanoscale Devices. , 2017, , 1-30.		0
9	Uncovering the temperature of the hotspot in nanoscale devices. , 2014, , .		4
10	Exploring the use of Cadence IC in Education. Electronics, 2014, 17, .	0.3	0
11	Inclusion of Phonon Dispersion and its Influence on Electrical Characteristic Degradation due to Heating Effects in Nanoscale FD-SOI Devices. , 2010, , .		0
12	Electrothermal Studies of FD SOI Devices That Utilize a New Theoretical Model for the Temperature and Thickness Dependence of the Thermal Conductivity. IEEE Transactions on Electron Devices, 2010, 57, 726-728.	3.0	30
13	First Self-Consistent Thermal Device Simulator. , 2010, , .		0
14	Modeling self-heating effects in 10nm channel length nanowire transistors. , 2010, , .		0
15	Self-Heating Effects in Nanoscale FD SOI Devices: The Role of the Substrate, Boundary Conditions at Various Interfaces, and the Dielectric Material Type for the BOX. IEEE Transactions on Electron Devices, 2009, 56, 3064-3071.	3.0	47
16	Modeling thermal effects in nano-devices. Journal of Computational Electronics, 2008, 7, 226-230.	2.5	9
17	Modeling Thermal Effects in Nanodevices. IEEE Transactions on Electron Devices, 2008, 55, 1306-1316.	3.0	107
18	Is SOD Technology the Solution to Heating Problems in SOI Devices?. IEEE Electron Device Letters, 2008, 29, 621-624.	3.9	34

#	ARTICLE	IF	CITATIONS
19	The role of the temperature boundary conditions on the gate electrode on the heat distribution in 25 nm FD-SOI MOSFETs with SiO ₂ and gate-stack (High-K Dielectric) as the gate oxide. , 2007, , .		1
20	Heating Effects in Nanoscale Devices. , 0, , .		9
21	Monte Carlo Device Simulations. , 0, , .		3